1. Consider an OPAMP with V_{DD}=5V, GND=0V and V_{ss}= -5V as shown in Fig.1.
   (a) If R_1=R_2=1kΩ and V_{in}=0V, please find that V_-=? V_o=? when the OPAMP is with 10 mV input offset and gain A=∞. (10%)(V_- is the inverting input node of the OPAMP)
   (b) If R_1=R_2=1kΩ and V_{in}==2V, please find that V_-=? V_o=? when the OPAMP is with 10 mV input offset and gain A=∞. (5%)
   (c) If R_1=1kΩ and R_2=1000kΩ, please find that A_F=V_o/V_{in}=? when the OPAMP is with no offset and gain A=100.(10%)

2. For the circuit shown in Fig.2, for the BJT, β=200 and $|V_A|$=100V, and for the MOSFET, $|V_A|$=30 V, $|V_t|$=1 V, k'(W/L) = 200 μA/V^2. Let I=20μA and V_{BIAS}=2V. Assume the current generator I to have the same resistance as the output resistance of its connected circuit and assume the current generator 2I to be ideal. Find
   (a) the bias current in Q1 (3%);
   (b) the voltage at the node between the two transistors (assume $|V_{BE}|$=0.7V)(3%);
   (c) g_m and r_o for each device (4%);
   (d) the maximum allowed value of v_o (3%);
   (e) the voltage gain(3%);
   (f) the input resistance(3%);
   (g) the output resistance(3%);
   (h) Does the current source 2I have to be a sophisticated one? For this generator, what output resistance would reduce the overall gain by 1%?(3%)

3. A TTL NAND gate with a totem-pole output is shown in Fig.3. Assume that the inputs are derived from the outputs of identical gates and β_F=100 and β_R=0.5.
   (a) Given A=B=C=V(1), determine the operation modes of transistors Q_1 and Q_4. (4%)
   (b) Repeat (a) for the situation where at least one input logic level is V(0). (4%)
   (c) Determine the logic levels. (8%)
   (d) Please estimate the average static power dissipation (P_{av}) and dynamic power dissipation (P_{dyn}) per gate. (9%)

4. (a) Draw the load line of D1 and find V1 for the circuit shown in Fig. 4. Assume that D1, D2 and D3 have the same I-V characteristics, and VA = 3Vr , where Vr is the cut-in voltage of the diode. (10%)
   (b) Derive and plot the small-signal equivalent circuit for a BJT with I-V characteristics expressed as $i_C = av_{BE}^2(1+bv_{CE})$, where a and b are constant. (5%)
   (c) Determine ID and VO for the circuit shown in Fig. 5 for VDD = 5 V and VI = 2 V. Assume that $k_{n1} = 5k_{n2} = 50\,\mu A/V^2$ and $V_{th1} = V_{th2} = 1\,V$, where $k_n (= 0.5\mu_n C_{ox}(W/L))$ is the conduction parameter and V_{th} is the threshold voltage. Note that T2 is an enhancement-mode MOSFET. (10%)

(背面仍有題目,請繼續作答)

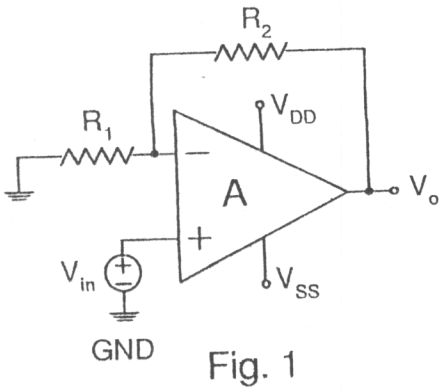

Fig. 1

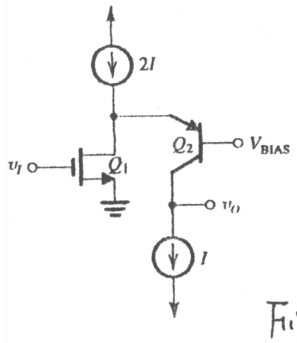

Fig. 2

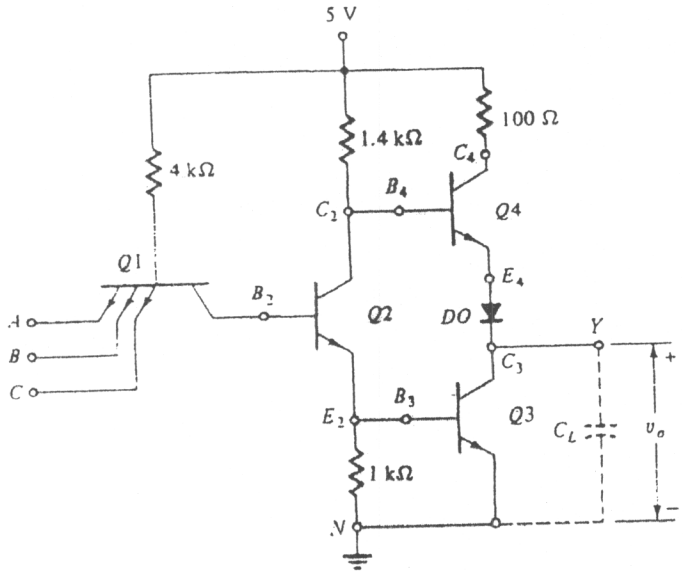

Fig. 3

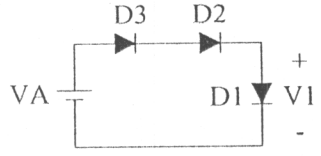

Fig. 4

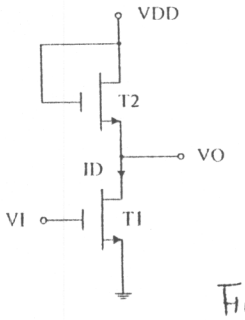

Fig. 5